

NPN BDX54 – BDX54A – BDX54B – BDX54C

SILICON POWER DARLINGTON TRANSISTORS

The BDX54, BDX54A, BDX54B and BDX54C are silicon epitaxial-base PNP transistors in monolithic Darlington configuration and are mounted in Jedec TO-220 plastic package. They are intented for use in audio amplifiers, medium power linear and switching applications. The complementary NPN types are the BDX53, BDX53A, BDX53B and BDX53C respectively. Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings			Value	Unit
V _{CEO}	Collector-Emitter Voltage	I _B =0	BDX54	-45	
			BDX54A	-60	V
			BDX54B	-80	V
			BDX54C	-100	
V _{CBO}		I _E =0	BDX54	-45	
	Callester Dess Valters		BDX54A	-60	V
	Collector-Base Voltage		BDX54B	-80	v
			BDX54C	-100	
V _{EBO}	Emitter-Base Voltage	I _C =0		-5	V
I _C	Collector Current	I _{C(RMS)}		-8	A
	Collector Current	I _{CM}		-12	A
I _B	Base Current			-0.2	А
Ρ _τ	Power Dissipation	@ $T_{C} = 25^{\circ}$		60	W
TJ	Junction Temperature			150	°C
Ts	Storage Temperature		-65 to +150	C	

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R _{thJ-C}	Thermal Resistance, Junction to Case	2.08	°C/W



NPN BDX54 – BDX54A – BDX54B – BDX54C

ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition	on(s)	Min	Тур	Мах	Unit
			BDX54	-45	-	-	
V _{CEO(SUS)}	Collector-Emitter Breakdown Voltage (*)	$I_{\rm C}$ =-100 mA $I_{\rm B}$ = 0	BDX54A	-60	-	-	V
			BDX54B	-80	-	-	
			BDX54C	-100	-	-	
		V_{CB} =-22V, I_{B} = 0	BDX54	-	-	_	_
I _{CEO}		V_{CB} =-30V, I_{B} = 0	BDX54A	-			
	Collector Cutoff Current	V_{CB} =-40V, I_{B} = 0	BDX54B	-	-	0.5	mA
		V_{CB} =-50V, I_{B} = 0	BDX54C	-	-		
	Emitter Cutoff Current	V _{BE} =-5 V	BDX54		-	-2	mA
_			BDX54A				
I _{EBO}			BDX54B				
			BDX54C				
		V_{CBO} =-45 V, I _E = 0	BDX54	-	-		
	Collector-Base Cutoff Current	V_{CBO} =-60 V, I _E = 0	BDX54A	-	-	-0.2	mA
СВО		V_{CBO} =-80 V, I _E = 0	BDX54B	-			
		V_{CBO} =-100 V, I _E = 0	BDX54C	- 1	-		
V _{CE(SAT)}	Collector-Emitter saturation Voltage (*)	$I_{\rm C}$ =-3 A, $I_{\rm B}$ =-12 mA	BDX54		-	-2	V
			BDX54A				
			BDX54B				
			BDX54C				
	Base-Emitter saturation Voltage (*)	I _C =-3 A, I _B =-12 mA	BDX54	-	-	-2.5	
V _{BE(SAT)}			BDX54A				
			BDX54B				
			BDX54C				
			BDX54				
			BDX54A				
		I _F =-3 A	BDX54B		-	-4.0	V
	Forward Voltage (pulse		BDX54C				
V _F	method)		BDX54		-1.8		V
		I _F =-8 A	BDX54A	- 1		-2.5	
			BDX54B	-	-2.5	-	
			BDX54C				
h _{FE}		V _{CE} =-3 V, I _C =-3 A	BDX54	750	-	-	-
	DC Current Gain (*)		BDX54A				
			BDX54B				
			BDX54C				

(*) Pulse Width $\approx 300~\mu s,$ Duty Cycle \angle 1.5%

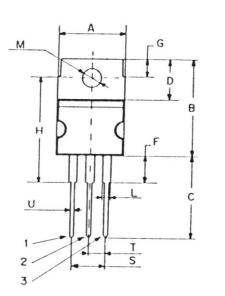


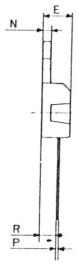
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MECHANICAL DATA CASE TO-220

DIMENSIONS (mm)				
	Min.	Max.		
A	9,90	10,30		
В	15,65	15,90		
B C D E F	13,20	13,40		
D	6,45	6,65		
E	4,30	4,50		
F	2,70	3,15		
G H L	2,60	3,00		
Н	15,75	17.15		
L	1,15	1,40		
М	3,50	3,70		
N	-	1,37		
Р	0,46	0,55		
R	2,50	2,70		
S	4,98	5,08		
S T	2.49	2.54		
U	0,70	0,90		

Pin 1 :	Base
Pin 2 :	Collector
Pin 3 :	Emitter
Case :	Collector





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